Electronic Supplementary Information

Metal-Insulator Transition in Multilayer MoS_2

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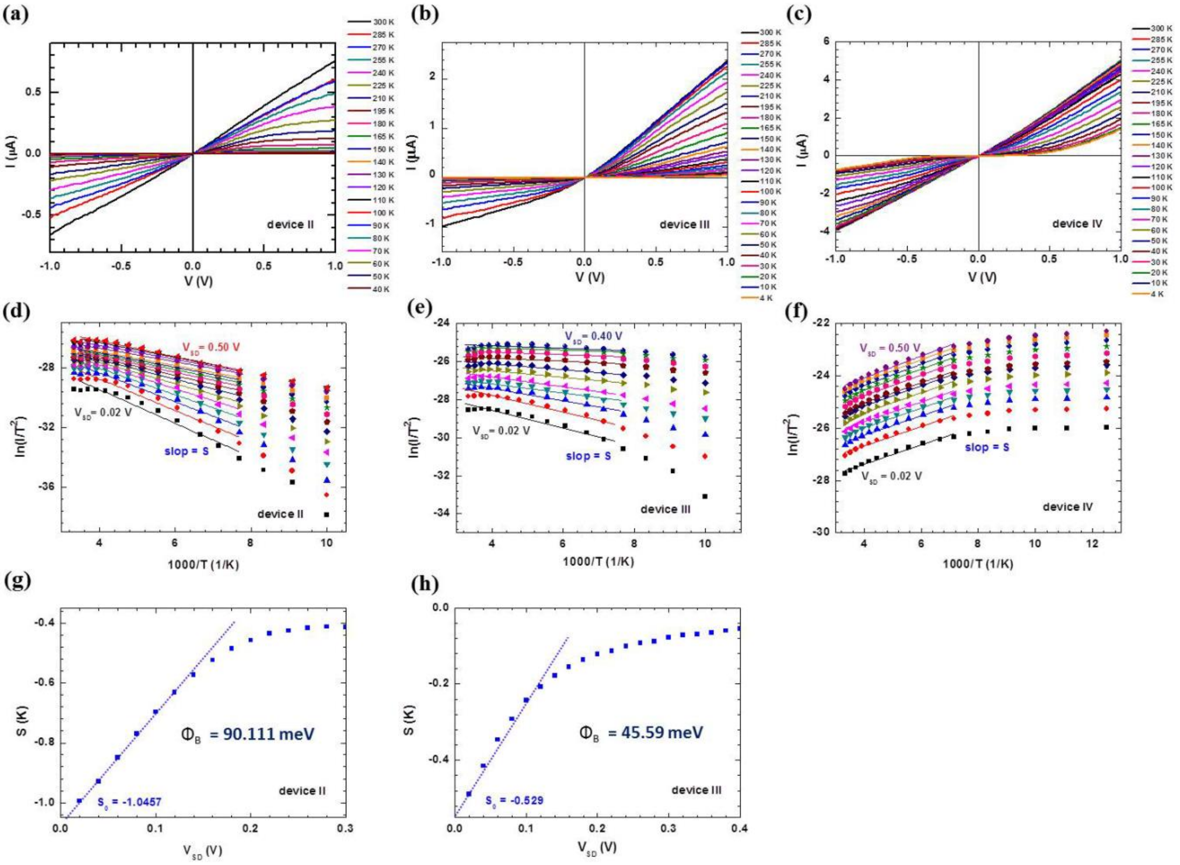

Figure S1 Temperature dependence of *I*-*V* curves measured for **(a)** device II, **(b)** device III, and **(c)** device IV. ln(I/T^2) versus 1000/*T* for **(d)** device II, **(e)** device III, and **(f)** device IV. Slope estimated from the plot of ln(I/T^2) versus 1000/*T* as a function of *V* for **(g)** device II and **(h)** device III.

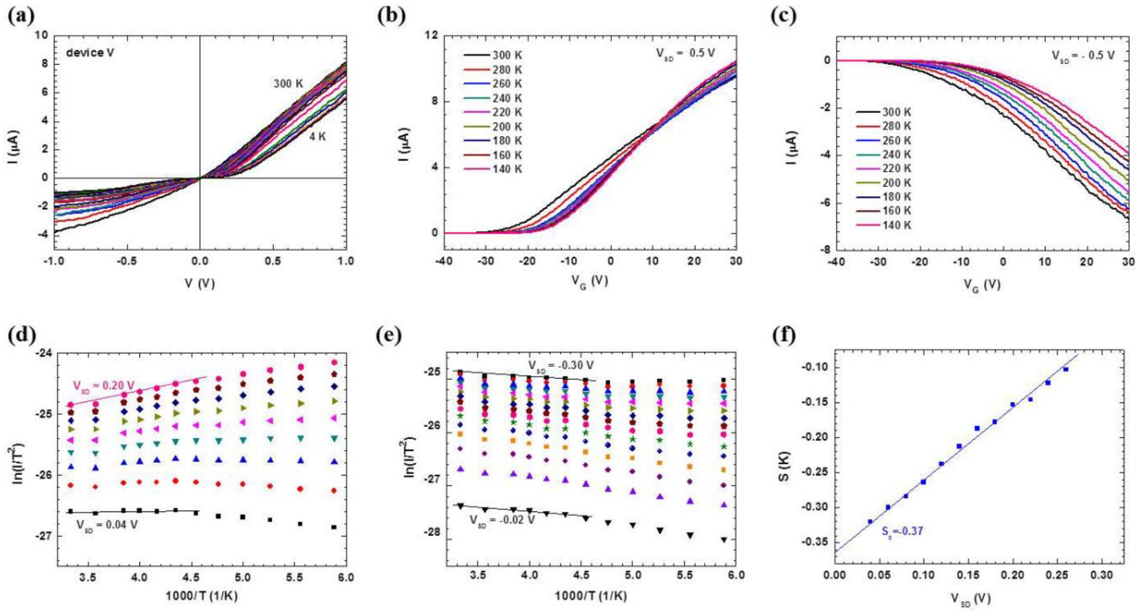

Figure S2 **(a)** *I*-*V* curves measured at different temperatures for device V. **(b)** *I*-V_G transfer curves of device V at different temperatures with **(b)** *V*=0.5 V and **(c)** *V*=-0.5 V. ln(I/T^2) vs 1000/*T* for **(d)** positive and **(e)** negative voltages. **(f)** Slope estimated from ln(I/T^2) versus 1000/*T* as a function of *V* for negative voltages.

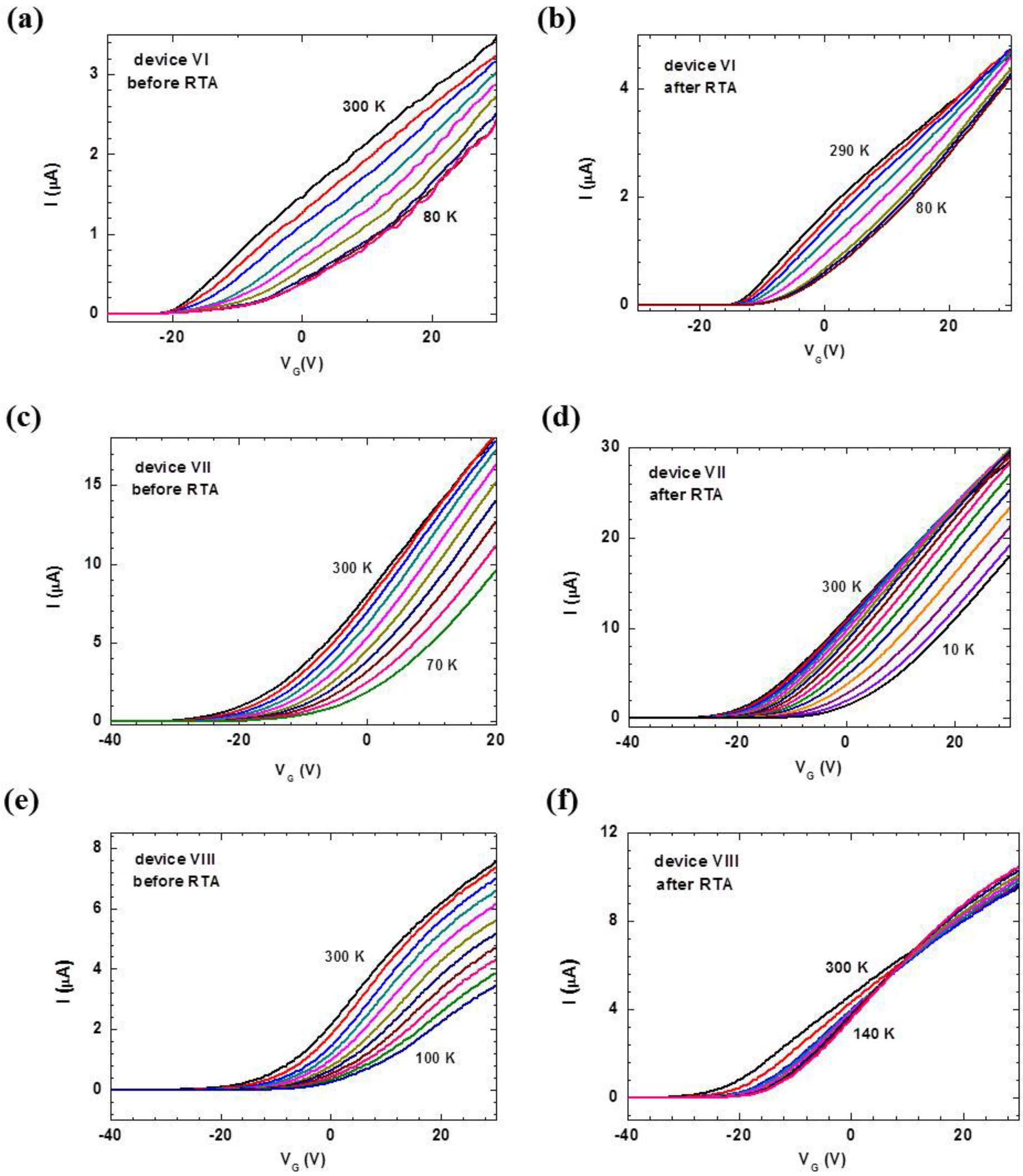

Figure S3. I-V_G transfer curves measured for devices VI (2.3 nm), VII (12 nm), and VIII (16 nm) with different thicknesses before **(a, c, e)** and after **(b, d, f)** RTA.